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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/693,847
		Filing Date	10/20/03
		First Named Inventor	August et al.
		Group Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned
		Attorney Docket Number	84,355
Sheet 2	of 2		

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials ¹	Cite No. ²	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		MCGREGOR et al, "Self-Biased Boron-10 Coated High-Purity Epitaxial GaAs Thermal Neutron Detector" IEEE transactions on nuclear science, vol. 47, no., August 2000	
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		ROBERTSON et al, "A class of boron-rich solid-state neutron detectors" Applied Physics Letters volume 80, number 19, 13 May 2002	
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		ARITA et al, "Experimental Investigation of Thermal Neutron-Induced Single Event Upset in Static Random Access Memories" Jpn. J. Appl. Phys Vol. 40 (2001) pp. L151-L153 Part 2, No. 2B, 15 February 2001	
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Examiner Signature	Date Considered
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